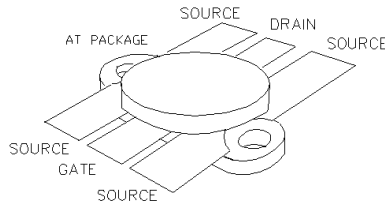




**General Description**

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"<sup>TM</sup> process features gold metal for greatly extended lifetime. Low output capacitance and high  $F_t$  enhance broadband performance



**PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR**

**80Watts Single Ended**

**Package Style AT**

**HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE**

**ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)**

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
150 Watts	1.2 °C/W	200 °C	-65 °C to 150 °C	8 A	70 V	70V	30V

**RF CHARACTERISTICS ( 80WATTS OUTPUT )**

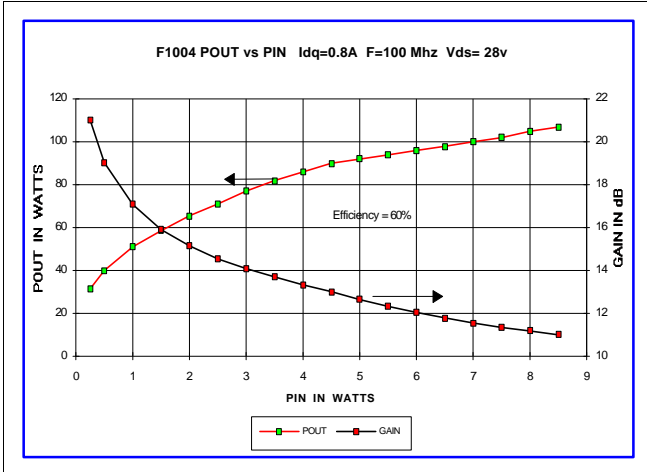
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	13			dB	Idq = 0.8 A, Vds = 28.0V, F = 175 MHz
$\eta$	Drain Efficiency		60		%	Idq = 0.8 A, Vds = 28.0V, F = 175 MHz
VSWR	Load Mismatch Toleranc			20:1	Relative	Idq = 0.8 A, Vds = 28.0V, F = 175 MHz

**ELECTRICAL CHARACTERISTICS (EACH SIDE)**

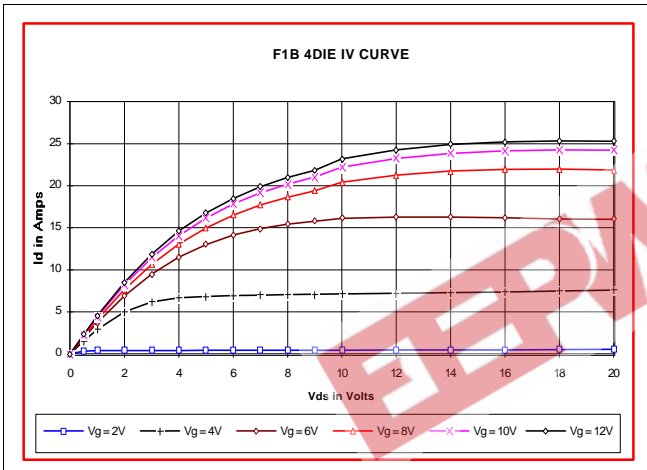
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltag	65			V	Ids = 0.2A, Vgs = 0V
Idss	Zero Bias Drain Curren			4	mA	Vds = 28.0 V, Vgs = 0V
Igss	Gate Leakage Curren			1	uA	Vds = 0 V, Vgs = 30V
Vgs	Gate Bias for Drain Curren	1		7	V	Ids = 0.4 A, Vgs = Vds
gM	Forward Transconductanc		3.2		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistanc		0.35		Ohm	Vgs = 20V, Ids = 16A
Idsat	Saturation Curren		22		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitanc		132		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitanc		16		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitanc		80		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz

# F1004

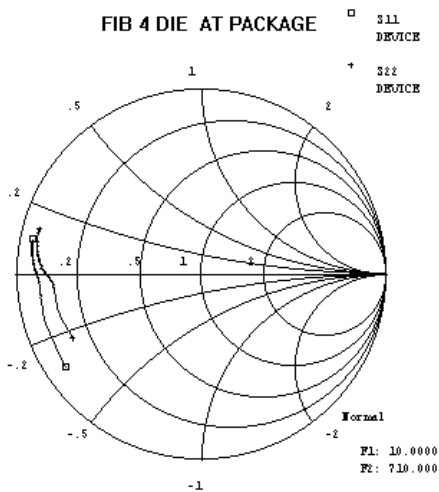
POUT VS PIN GRAPH



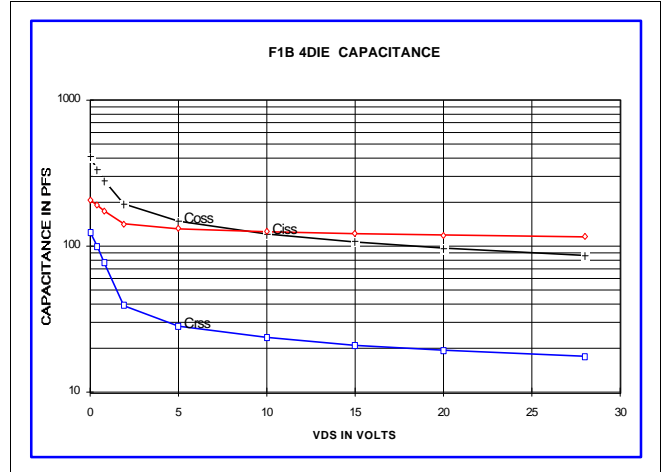
IV CURVE



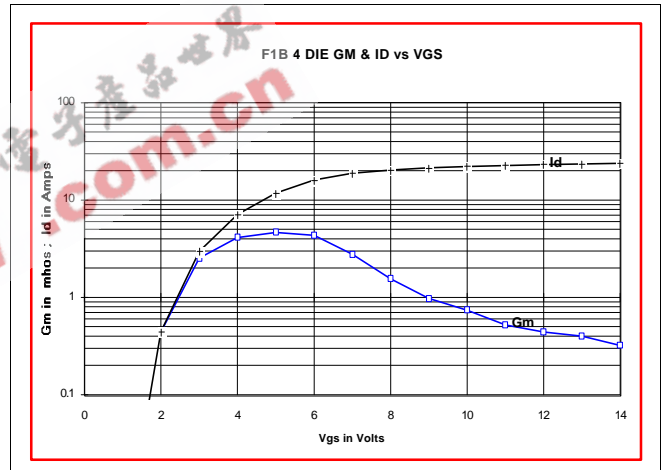
S11 AND S22 SMITH CHART



CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



PACKAGE DIMENSIONS IN INCHES

